



DRIE



Description

The Corial 200IL – Deep reactive ion etching (DRIE) machine is used for anisotropic dry etch of vertical hollow structures in various materials, such as silicon dioxide, silicon nitride, Sapphire , SiC , and various metals. The material is reactively etched by reactive substances in plasma similarly to more simple RIE (reactive ion etching) case while, in contrast to RIE, active ions move in main in the normal to substrate direction, owing action of inductively coupled plasma (ICP) and DC bias potentials.

Specifications / Capabilities

Wafer size : max. 4 inch without cooling and Bais ; 2 inch with cooling

Wafer thickness: max. 8mm

Maximal RF power is limited to 300 W and ICP power -1000W.

Standard tolerance: 10-15%

Available Gases

O₂ (oxygen)

SF₆ (sulfur hexafluoride)

CHF₃ (trifluoromethane)

Ar (Argon)

BCl₃ (Boron trichloride)

Cl₂ (Chlorine)

C₂H₄ (Ethylene)

H₂(Helium)

Link

<http://www.corial.net/>

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